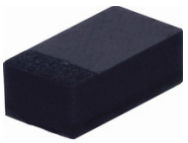
SMD Schottky Barrier Diode

COMCHIP
SMD Diodes Specialist

CDBFR001A (RoHs Device)

Io = 100mA
V_R = 30 Volts



Features

- Designed for mounting on small surface.
- Extremely thin package.
- Low stored charge.
- Majority carrier conduction.

Mechanical data

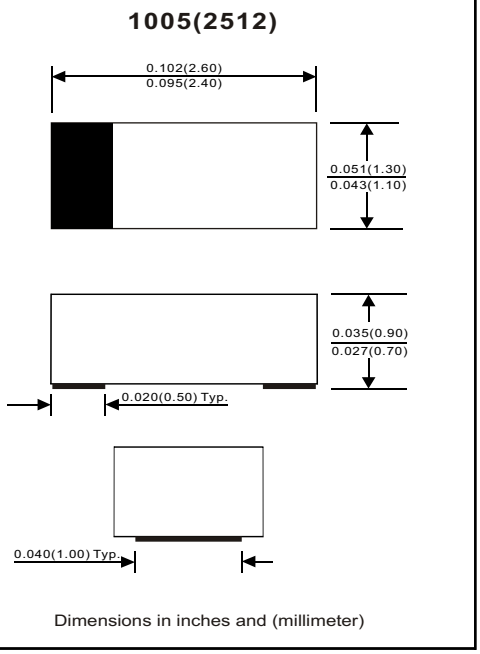
Case: 1005(2512) standard package, molded plastic.

Terminals: Gold plated, solderable per MIL-STD-750,method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any

Weight: 0.006 gram(approx.).



Maximum Rating (at T_A=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive Peak reverse voltage		V_{RRM}, V_R			30	V
Average forward current		I_O			100	mA
Forward current,surge peak	8.3 ms single half sine-wave superimposed on rate load(JEDEC method)	I_{FSM}		500		mA
Power Dissipation		P_D			150	mW
Sunction temperature		T_{STG}	-40		+125	°C
Junction temperature		T_j			+125	°C

Electrical Characteristics (at T_A=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage 1	I_F = 0.1 mA DC	V_F			0.24	V
Forward voltage 2	I_F = 1 mA DC	V_F			0.32	V
Forward voltage 3	I_F = 10 mA DC	V_F			0.40	V
Forward voltage 4	I_F = 30 mA DC	V_F			0.50	V
Forward voltage 5	I_F = 100 mA DC	V_F			1.00	V
Reverse current	V_R = 25V	I_R			2	uA
Capacitance between terimnals	F = 1 MHZ and 10 VDC reverse voltage	C_T			6	pF

RATING AND CHARACTERISTIC CURVES (CDBFR001A)

Fig. 1 - Forward characteristics

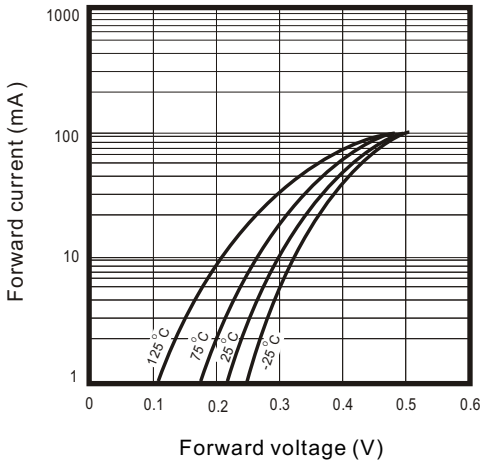


Fig. 2 - Reverse characteristics

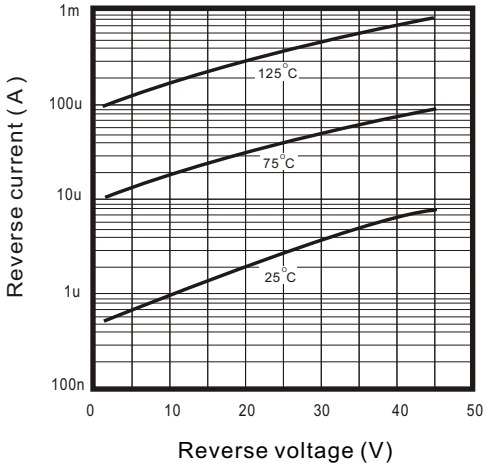


Fig.3 - Capacitance between terminals characteristics

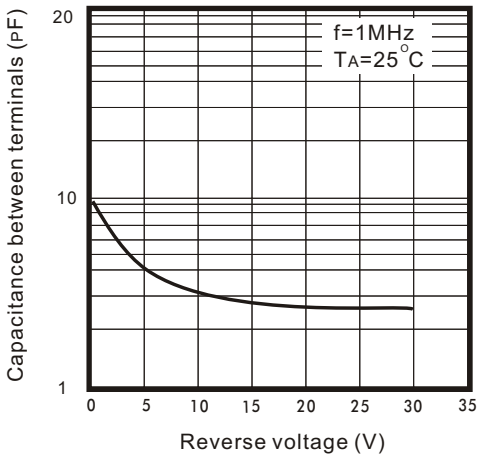


Fig.4 - Current derating curve